Investigation of Discrete Reactant Feeding for Atomic Layer Deposition of In_2O_3 Using Novel Alkyl-Cyclopentadienyl Indium precursor

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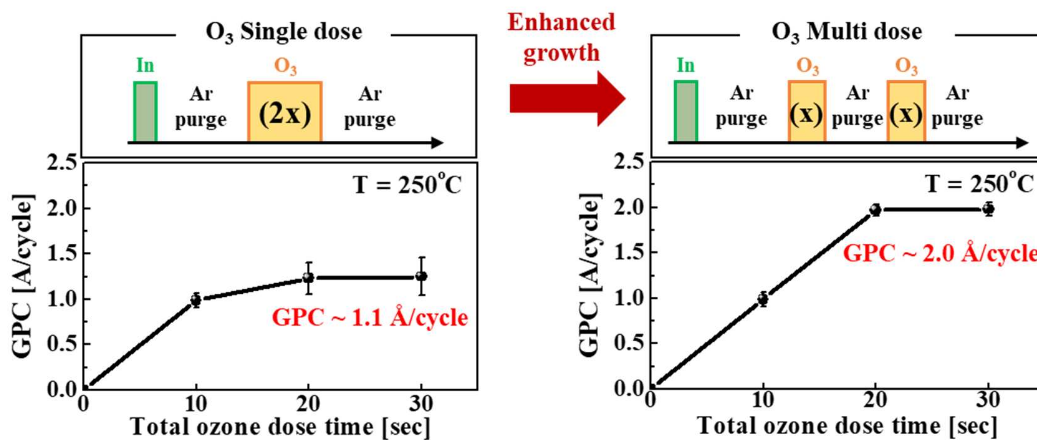

Figure 1. Boost the growth rate of ALD In_2O_3 films by applying the discrete reactant feeding method.

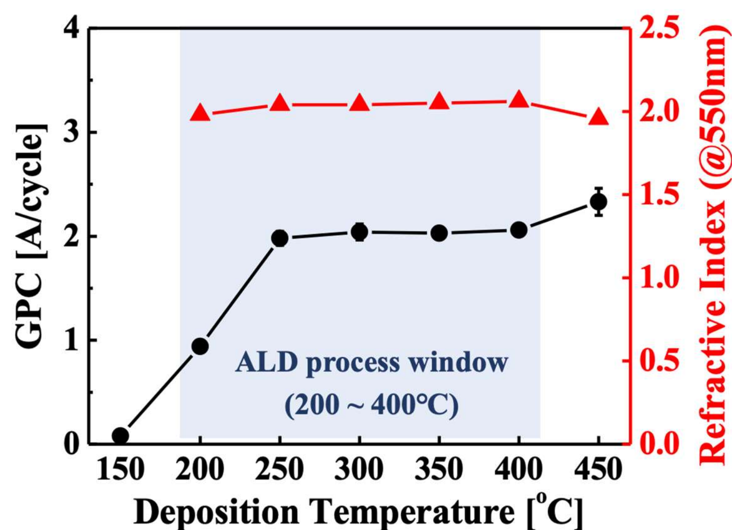

Figure 2. Broad ALD process window from 200℃ to 400℃